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December 12, 2003

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572 28 Davis Avenue Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/664,211 09/17/03

Purakh Raj Verma et al.

A METHOD OF MAKING DIRECT CONTACT ON GATE BY USING DIELECTRIC STOP LAYER

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on December (9, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

- U.S. Patent 5,731,239 to Wong et al., "Method of Making Self-Aligned Silicide Narrow Gate Electrodes for Field Effect Transistors Having Low Sheet Resistance," describes a method for making low sheet resistance sub quarter micrometer gate electrode in FET devices.
- U.S. Patent 6,010,954 to Ho et al., "CMOS Gate Architecture for Integration of Salicide Process in Sub 0.1uM Devices," describes a method to form a "mushroom shaped" gate structure that increases the top gate silicide contact area and improves the salicidation process.
- U.S. Patent 6,271,087 to Kinoshita et al., "Method for Forming Self-Aligned Contacts and Local Interconnects Using Self-Aligned Local Interconnects," describes a method for forming self-aligned contacts and local interconnects.
- U.S. Patent 6,281,059 to Cheng et al., "Method of Doing ESD Protective Device Ion Implant Without Additional Photo Mask," describes a method of forming ESD protective transistor.

Sincerely

Stephen B. Ackerman,

Reg. No. 37761

IN AN APPLICATION (Uso sovoral showls if nocessary) U. S. PATENT DOCUMENTS CXAMINGE NAME CAMIN HOSCIALE FAME 5731 23913/2498 Wang et al. 438 296 1/22 60109541/4/00 Ho et al. 438 596 9/12 6271 0878/7/01 Ki noshita et al. 438 258 10/1 6281 0598/28/01 Cheng et al. 438 200 5/1	Form PTO-										CS-			10/66	4,2	J
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citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.